

## SIPMOS® Power-Transistor

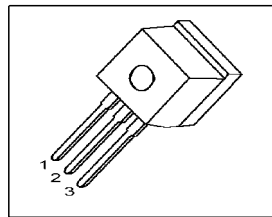
### Feature

- N-Channel
- Enhancement mode
- Logic Level
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

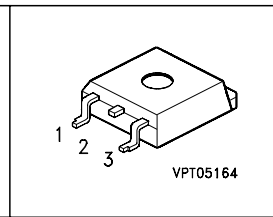
### Product Summary

$V_{DS}$	100	V
$R_{DS(on)}$	14	mΩ
$I_D$	80	A

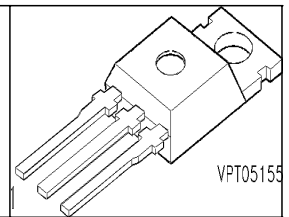
P-TO262-3-1



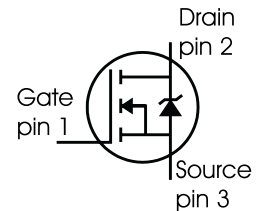
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP80N10L	P-TO220-3-1	Q67042-S4173	80N10L
SPB80N10L	P-TO263-3-2	Q67042-S4171	80N10L
SPI80N10L	P-TO262-3-1	Q67042-S4172	80N10L



### Maximum Ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	$I_D$	80	A
$T_C=25\text{ °C}$		80	
$T_C=100\text{ °C}$		58	
Pulsed drain current	$I_D \text{ puls}$	320	
$T_C=25\text{ °C}$			
Avalanche energy, single pulse	$E_{AS}$	700	mJ
$I_D=80\text{ A}$ , $V_{DD}=25\text{ V}$ , $R_{GS}=25\text{ Ω}$			
Avalanche energy, periodic limited by $T_{jmax}$	$E_{AR}$	25	
Reverse diode dv/dt	dv/dt	6	kV/μs
$I_S=80\text{ A}$ , $V_{DS}=0\text{ V}$ , $di/dt=200\text{ A/μs}$			
Gate source voltage	$V_{GS}$	±20	V
Power dissipation	$P_{tot}$	250	W
$T_C=25\text{ °C}$			
Operating and storage temperature	$T_j, T_{stg}$	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62.5	
SMD version, device on PCB:	$R_{thJA}$				
@ min. footprint		-	-	62	
@ 6 cm <sup>2</sup> cooling area <sup>1)</sup>		-	-	40	

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain-source breakdown voltage $V_{GS}=0V, I_D=2mA$	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 2\text{ mA}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=100V, V_{GS}=0V, T_j=25^\circ\text{C}$ $V_{DS}=100V, V_{GS}=0V, T_j=150^\circ\text{C}$	$I_{DSS}$	-	0.1	1	$\mu\text{A}$
		-	-	100	
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	$I_{GSS}$	-	10	100	nA
Drain-source on-state resistance $V_{GS}=4.5V, I_D=58A$	$R_{DS(on)}$	-	15	24	m $\Omega$
Drain-source on-state resistance $V_{GS}=10V, I_D=58A$	$R_{DS(on)}$	-	11	14	

<sup>1)</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic Characteristics**

Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 58\text{A}$	26	52	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	3630	4540	pF
Output capacitance	$C_{oss}$		-	640	800	
Reverse transfer capacitance	$C_{rss}$		-	345	430	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{V}$ , $V_{GS} = 10\text{V}$ , $I_D = 80\text{A}$ , $R_G = 1.6\Omega$	-	14	21	ns
Rise time	$t_r$		-	60	90	
Turn-off delay time	$t_{d(off)}$		-	82	123	
Fall time	$t_f$		-	20	30	

**Gate Charge Characteristics**

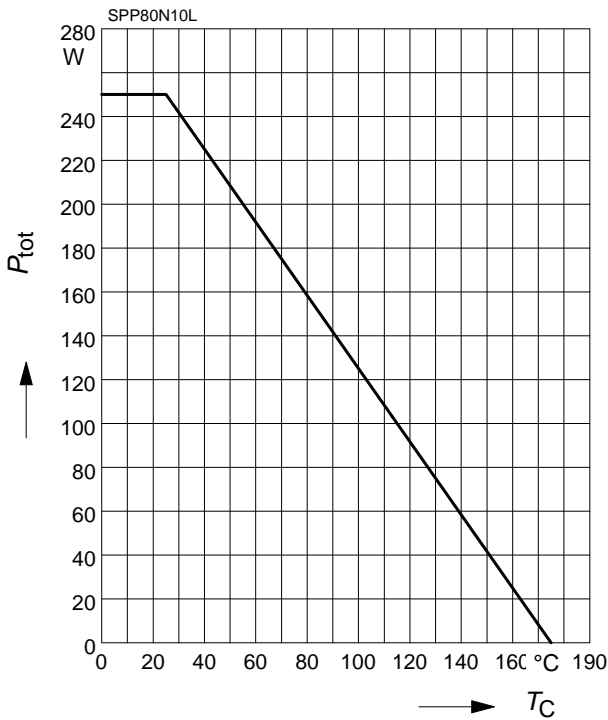
Gate to source charge	$Q_{gs}$	$V_{DD} = 80\text{V}$ , $I_D = 80\text{A}$	-	14	21	nC
Gate to drain charge	$Q_{gd}$		-	65	98	
Gate charge total	$Q_g$	$V_{DD} = 80\text{V}$ , $I_D = 80\text{A}$ , $V_{GS} = 0$ to $10\text{V}$	-	160	240	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 80\text{V}$ , $I_D = 80\text{A}$	-	4.2	-	V

**Reverse Diode**

Inverse diode continuous forward current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	80	A
Inv. diode direct current, pulsed	$I_{SM}$		-	-	320	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0\text{V}$ , $I_F = 80\text{A}$	-	0.9	1.3	V
Reverse recovery time	$t_{rr}$	$V_R = 50\text{V}$ , $I_F = I_S$ , $di_F/dt = 100\text{A}/\mu\text{s}$	-	95	140	ns
Reverse recovery charge	$Q_{rr}$		-	330	500	

### 1 Power dissipation

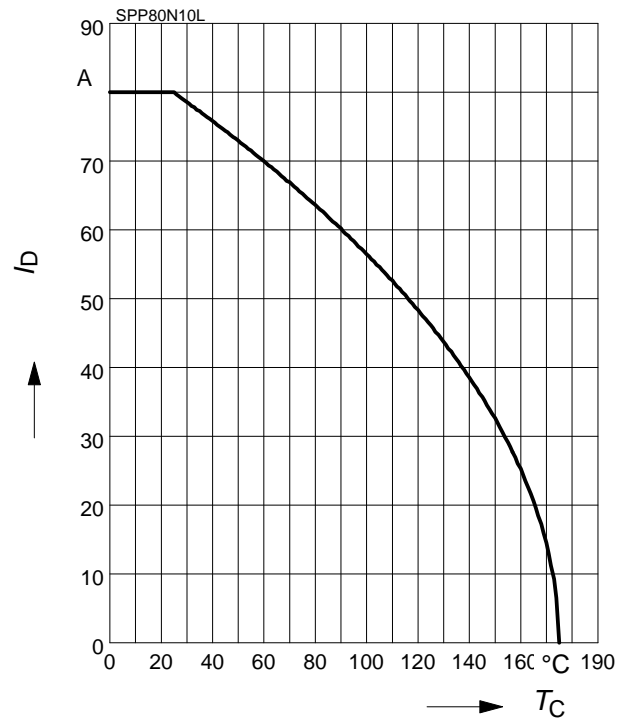
$$P_{tot} = f(T_C)$$



### 2 Drain current

$$I_D = f(T_C)$$

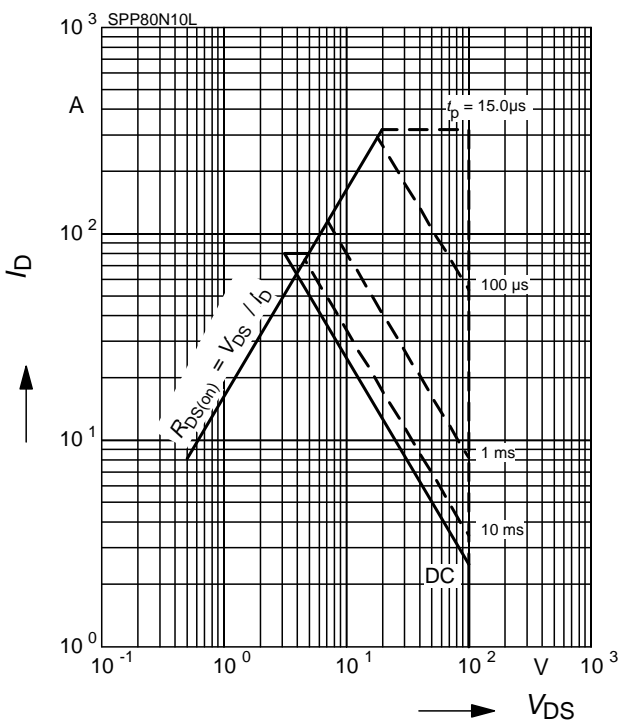
parameter:  $V_{GS} \geq 10 \text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

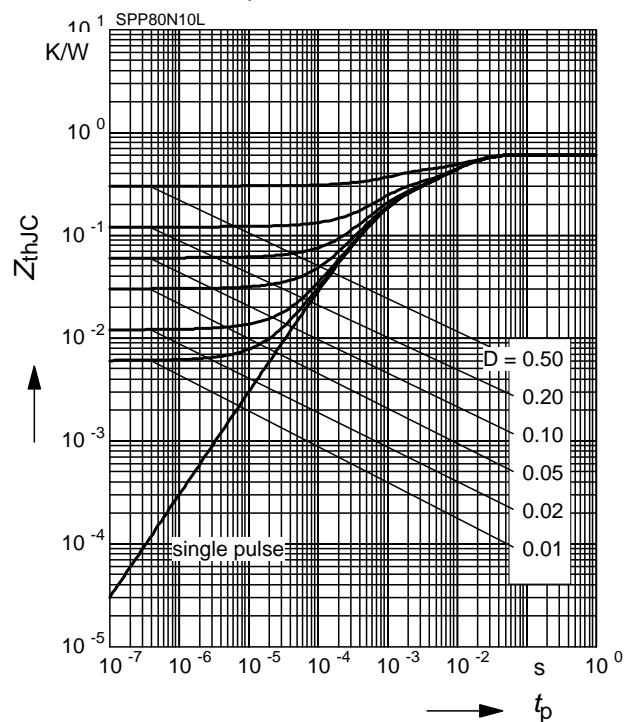
parameter:  $D = 0, T_C = 25 \text{ °C}$



### 4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

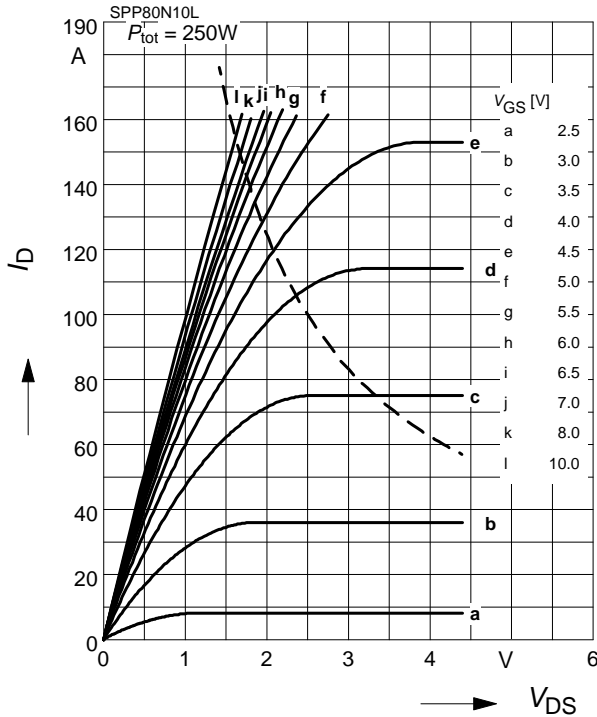
parameter:  $D = t_p/T$



### 5 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

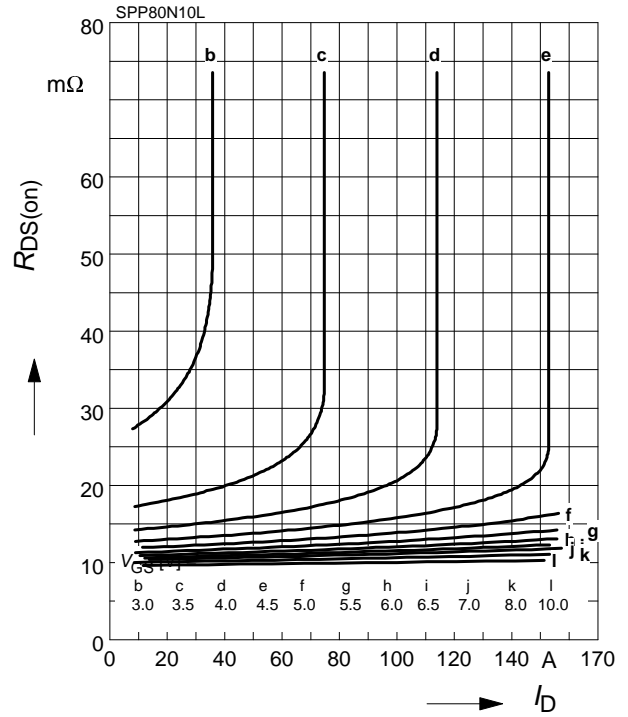
parameter:  $t_p = 80 \mu\text{s}$



### 6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

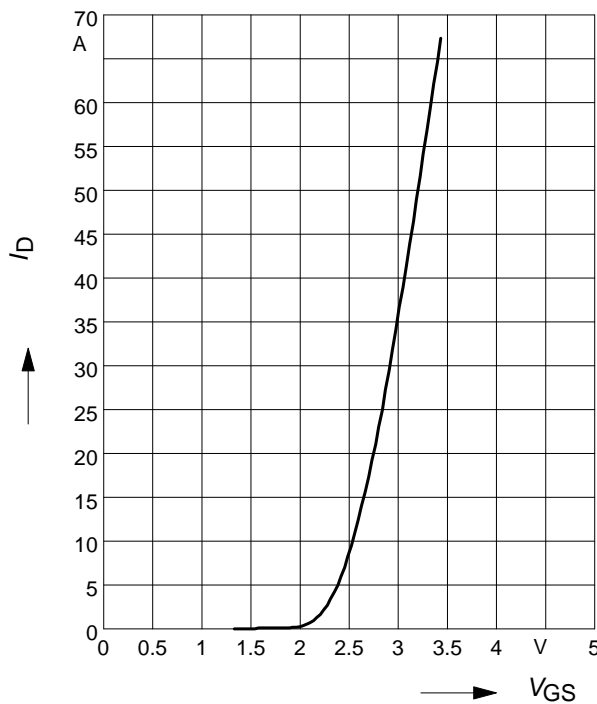
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

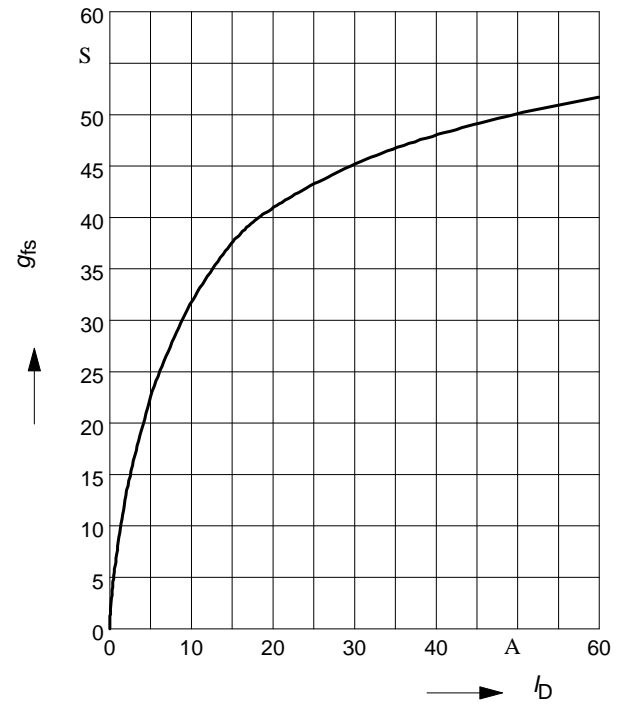
parameter:  $t_p = 80 \mu\text{s}$



### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$

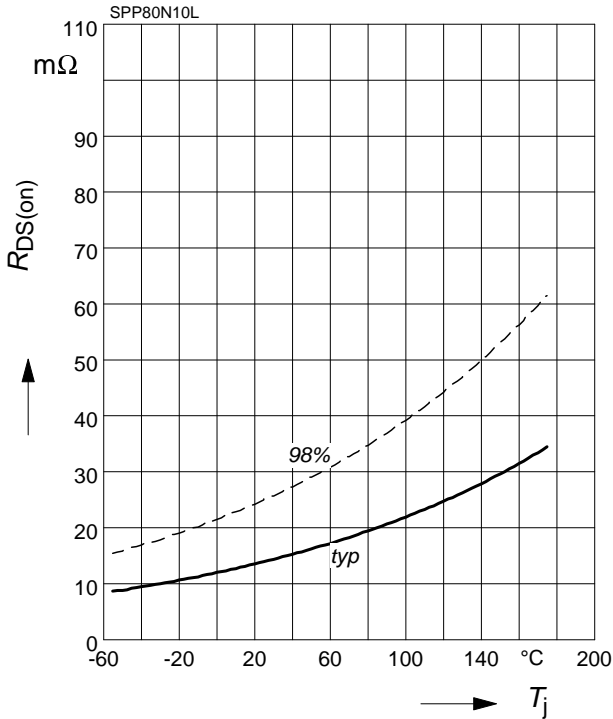
parameter:  $g_{fs}$



### 9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

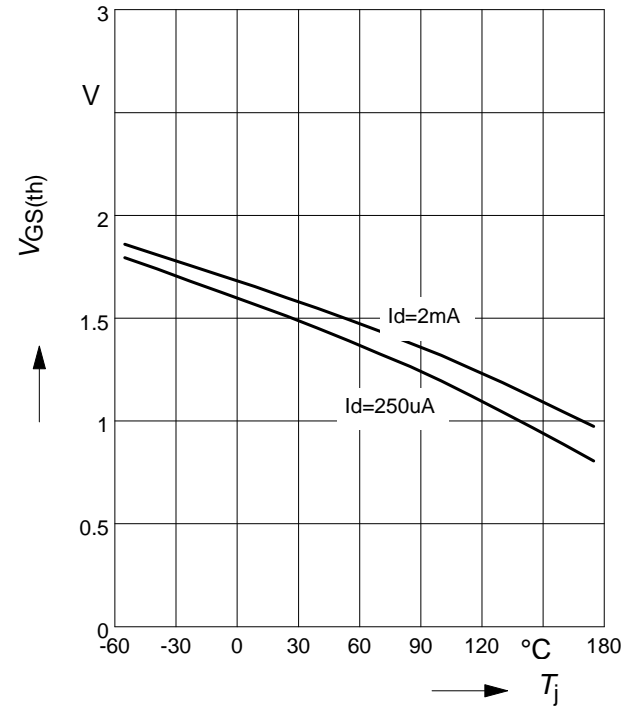
parameter:  $I_D = 58 \text{ A}$ ,  $V_{GS} = 4.5 \text{ V}$



### 10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

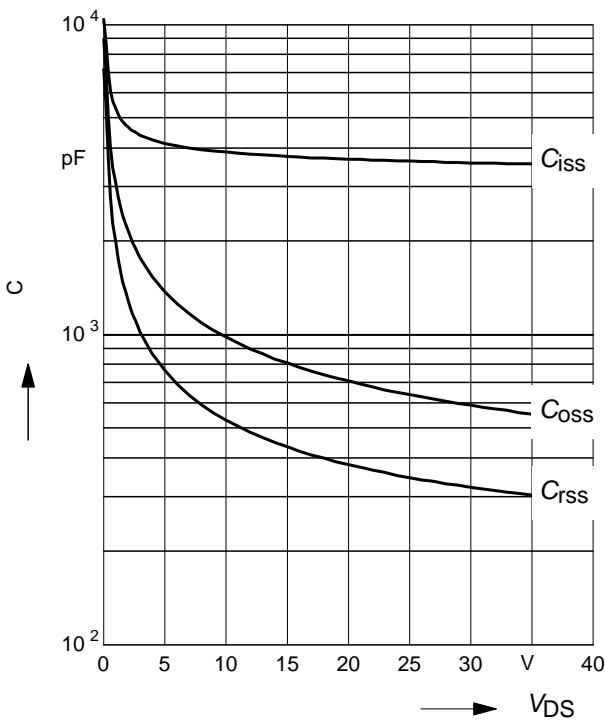
parameter:  $V_{GS} = V_{DS}$



### 11 Typ. capacitances

$$C = f(V_{DS})$$

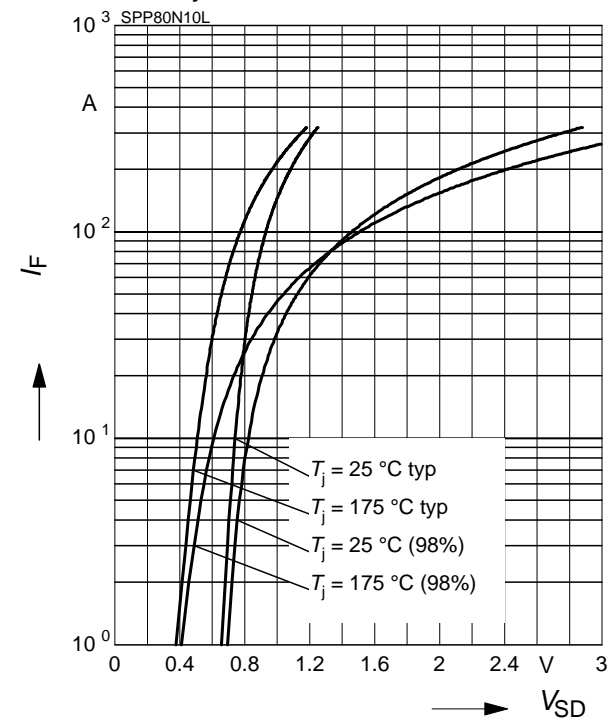
parameter:  $V_{GS} = 0 \text{ V}$ ,  $f = 1 \text{ MHz}$



### 12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

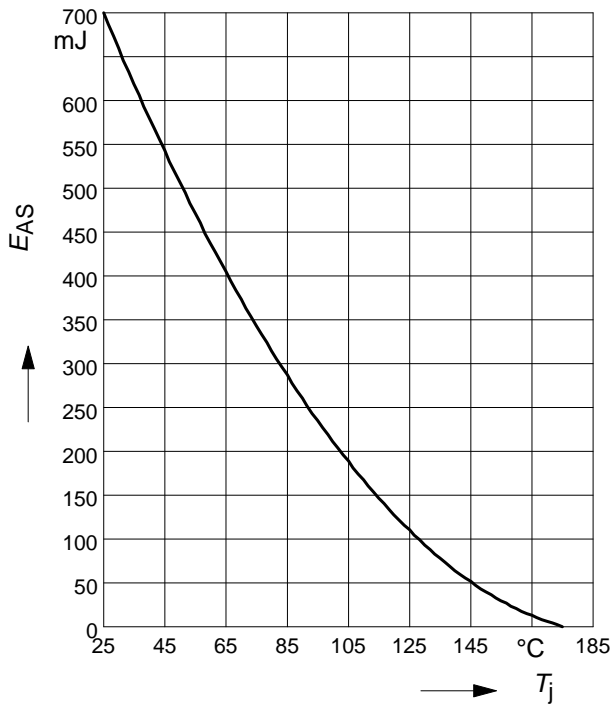
parameter:  $T_j$ ,  $t_p = 80 \mu\text{s}$



**13 Typ. avalanche energy**

$$E_{AS} = f(T_j)$$

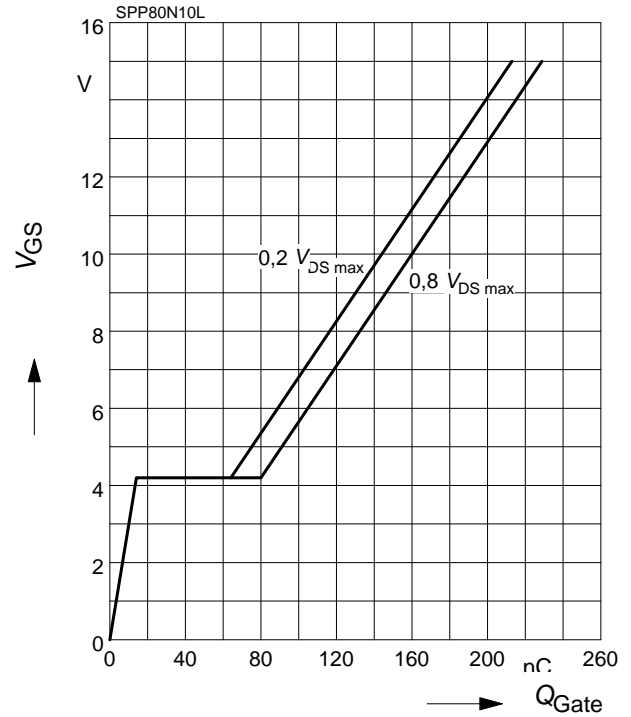
par.:  $I_D = 80 \text{ A}$  ,  $V_{DD} = 25 \text{ V}$ ,  $R_{GS} = 25 \Omega$



**14 Typ. gate charge**

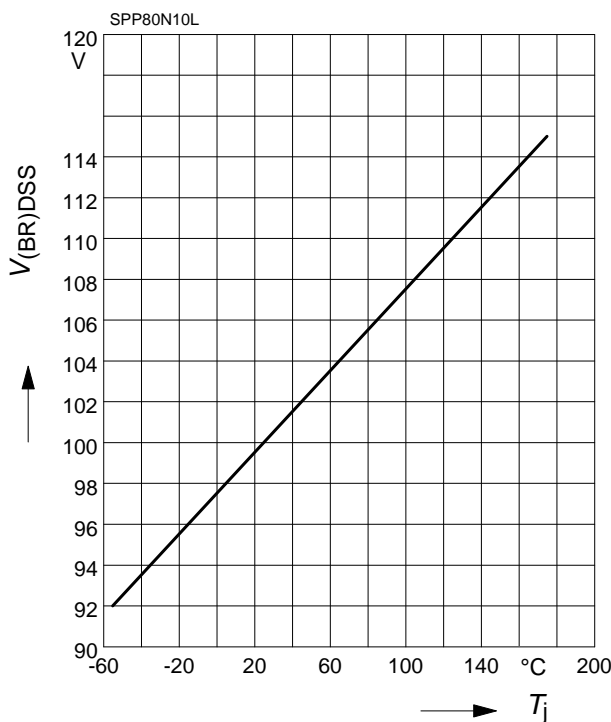
$$V_{GS} = f(Q_{Gate})$$

parameter:  $I_D = 80 \text{ A}$  pulsed



**15 Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$



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**Further information**

Please notice that the part number is BSPP80N10L, BSPB80N10L and BSPI80N10L, for simplicity the device is referred to by the term SPP80N10L, SPB80N10L and SPI80N10L throughout this documentation